

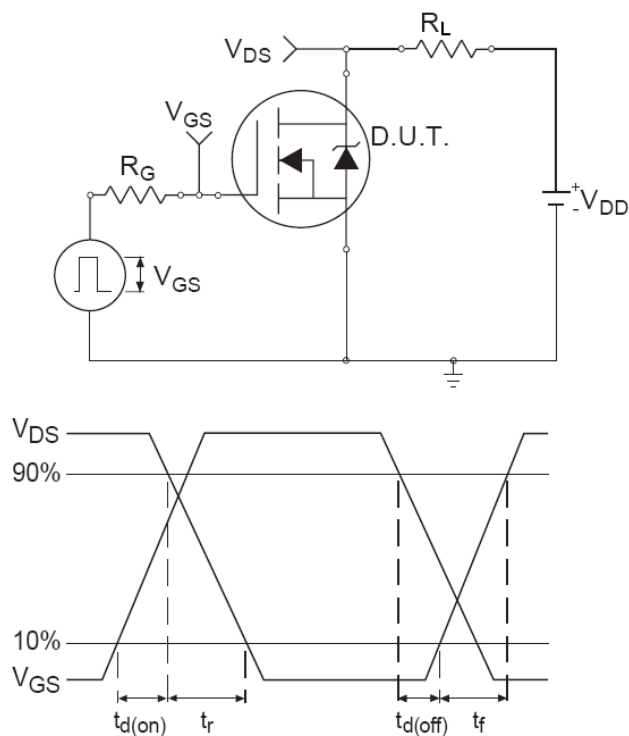
## Features

- $V_{DS}=70V / V_{GS}=\pm 25V / I_D=114A$   
 $R_{DS(ON)}=8m\Omega(max.)@V_{GS}=10V$
- Low Dense Cell Design
- Reliable and Rugged
- Advanced trench process technology "

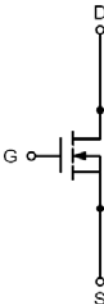
## Applications

- Synchronous Rectification
- Power Management in Inverter System

## Switching Time Test Circuit and Waveforms



## Pin Description



## Marking and pin Assignment



TO-220-3L top view

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM3307B	HM3307B	TO-220-3L	-	-	-

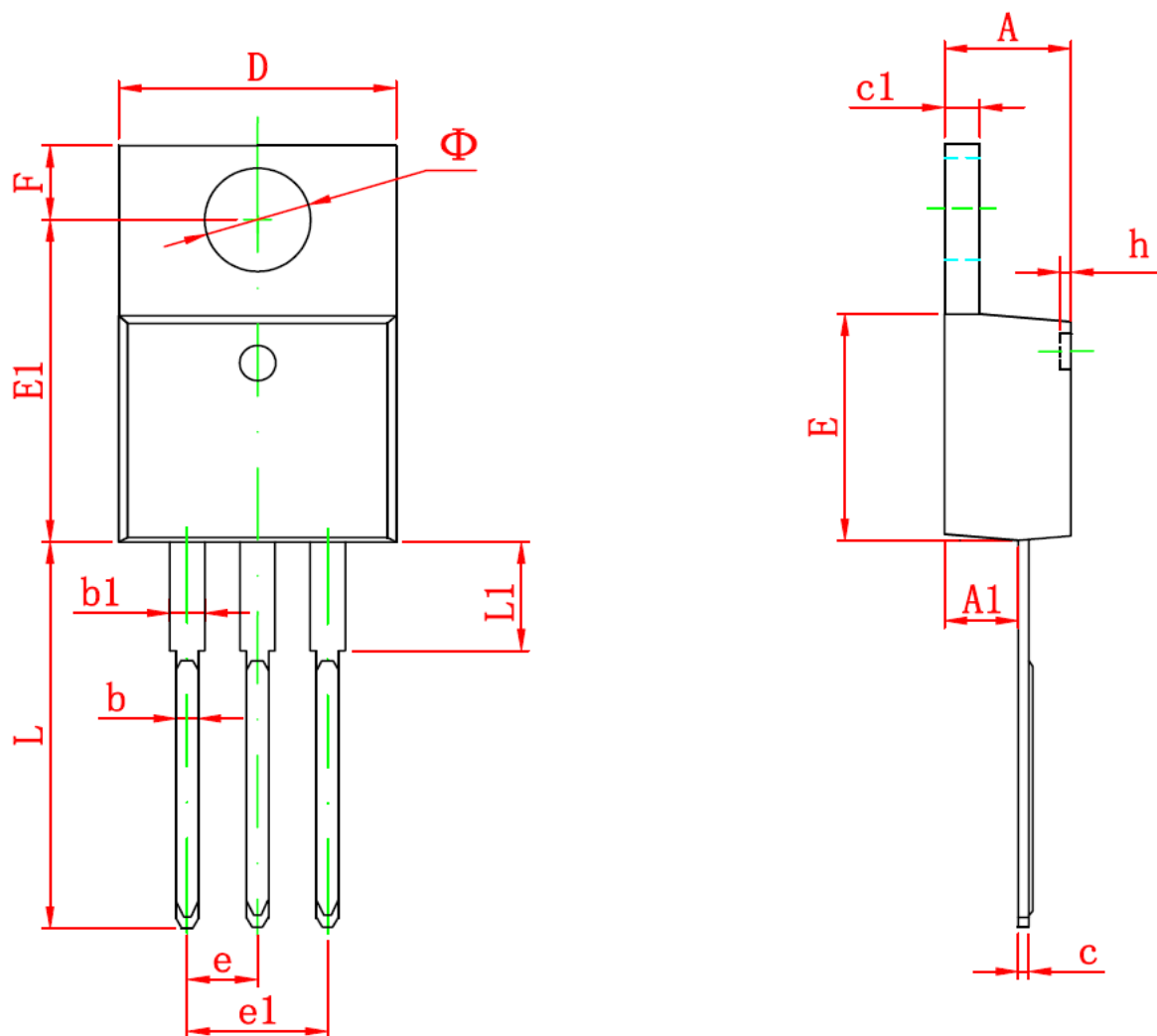
**Electrical Characteristics of CP Test** (TA=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ	Max.	Unit
<b>Static Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	70			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =64V, V <sub>GS</sub> =0V			1	uA
		T <sub>J</sub> =85°C			30	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	3.1	4	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±25V, V <sub>DS</sub> =0V			±100	nA
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =40A		6.3	8	mΩ
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> =30A, V <sub>GS</sub> =0V			1.3	V
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, Frequency=1MHz		1.6		Ω

Note: 1: Pulse test ; pulse width ≤ 300ns, duty cycle ≤ 2%.

2: Guaranteed by design, not subject to production testing.

TO-220-3L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.470	4.670	0.176	0.184
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
E1	12.060	12.460	0.475	0.491
e	2.540 TYP		0.100 TYP	
e1	4.980	5.180	0.196	0.204
F	2.590	2.890	0.102	0.114
h	0.000	0.300	0.000	0.012
L	13.400	13.800	0.528	0.543
L1	3.560	3.960	0.140	0.156
Φ	3.735	3.935	0.147	0.155

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